

ABSTRACT

The inventive method for producing a silicon-on insulator structure consists in implanting hydrogen in a silicon plate (1), chemically treating said silicon plate (1) and a substrate (3), in connecting and grafting the silicon plate (1) and the substrate (3) and in layering along the implanted layer (2) of the plate (1). The drying, removal of physically adsorbed substances from the surface of the plate (1) and the substrate (3), connection of the plate (1) and the substrate (3), the grafting and layering thereof along the implanted layer (2) of the plate is carried out after the chemical treatment in one stage, in a low vacuum, at a temperature when hydrogen introduced by implantation remains in a bound state.